

## Electronic Acknowledgement Receipt

<b>EFS ID:</b>	9940759
<b>Application Number:</b>	10561299
<b>International Application Number:</b>	
<b>Confirmation Number:</b>	3881
<b>Title of Invention:</b>	Integrated circuit on high performance chip
<b>First Named Inventor/Applicant Name:</b>	Jean-Pierre Joly
<b>Customer Number:</b>	90678
<b>Filer:</b>	Jasper W. Dockrey/Maggie Pleczonka
<b>Filer Authorized By:</b>	Jasper W. Dockrey
<b>Attorney Docket Number:</b>	9905/34 (BIF023273US)
<b>Receipt Date:</b>	26-APR-2011
<b>Filing Date:</b>	15-DEC-2005
<b>Time Stamp:</b>	12:14:18
<b>Application Type:</b>	U.S. National Stage under 35 USC 371

### Payment information:

Submitted with Payment	no
------------------------	----

### File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	NPL Documents	Blanchard-Lagahae-C-Hydrogen-and-Hellum.pdf	584601 9c862b1b428d371013f42b80c19c94b57 f31	no	13

### Warnings:

### Information:

2	NPL Documents	BlochI_P_et_al.pdf	290290 4a7b7851842e50388d42945bde513c5a7a8d4	no	4
Warnings:					
Information:					
3	NPL Documents	Borgatti_Stephen_The_Root-Mean_Square.pdf	44565 6b4b4e098f9560ba73805a157564d44848b77	no	1
Warnings:					
Information:					
4	NPL Documents	Bruel_et_al_1997_1636-1641.pdf	374214 a42a89798c14a784fe35485dc5714177a72ff	no	6
Warnings:					
Information:					
5	NPL Documents	Bruel_M_et_al_Vol_99-1_Meeting_Abstract.pdf	127811 37ed122e082852c05a24ebc107e3d846c04e956	no	2
Warnings:					
Information:					
6	NPL Documents	Bruel_M_Silicon_on_Insulator_Material.pdf	118402 625abdfcd413481791e485affb61728105d87a	no	2
Warnings:					
Information:					
7	NPL Documents	Bruel_M_Silicon_on_insulator_material_technology.pdf	123231 0b1c5f8edcd6dc1e728ba8e99942f1318e1b	no	2
Warnings:					
Information:					
8	NPL Documents	Bruel_M_Smart_Cut_A_New_SOI_Material_Technology.pdf	2170085 7b80eb136c26abac7e76750e973a7b147c5bb5c	no	25
Warnings:					
Information:					
9	NPL Documents	Bruel_M_Smart_Cut_A_Promising_New_SOI.pdf	122154 f172cc4f8b125c55a79c93928ba763c1ad76d0	no	2
Warnings:					
Information:					
10	NPL Documents	Bruel_M_Smart_Cut_Process.pdf	2566926 727a664329ca3a2b0c4d0c05dc0c61121918f54	no	26
Warnings:					
Information:					

11	NPL Documents	Bruel_Michel_Application_of_Hydrogen_on_Beams_to_Silicon.pdf	483916 dd52908cc824ccc32962cd44248f58e653b53d	no	7
<b>Warnings:</b>					
<b>Information:</b>					
12	NPL Documents	Camperi-Ginestet_et_al_Alignable_Epitaxial_Liftoff.pdf	312927 688761311bd75dbd84b6e6637d1ac2752c37a7	no	4
<b>Warnings:</b>					
<b>Information:</b>					
13	NPL Documents	Canham_et_al.pdf	217996 ea0f15d4ecc42cd2862e72a7980d1389294428f3	no	5
<b>Warnings:</b>					
<b>Information:</b>					
14	NPL Documents	Carter_et_al_107-114.pdf	669972 3188478849c3a661b4968c5823a6f18615b5408	no	8
<b>Warnings:</b>					
<b>Information:</b>					
15	NPL Documents	Carter-et-al_30-36.PDF	600857 2313c4539fcc73888385d3d6dc82467d2ab62	no	13
<b>Warnings:</b>					
<b>Information:</b>					
16	NPL Documents	Cassidy.pdf	195180 44be92241cda38d4a7fb0f99db81432081b37e	no	3
<b>Warnings:</b>					
<b>Information:</b>					
17	NPL Documents	Cerofolini_et_al_1992.pdf	674531 b4fc56a2af65d052e44899c2833055a55ae4d63	no	10
<b>Warnings:</b>					
<b>Information:</b>					
18	NPL Documents	Cerofolini_et_al_2000_1-52.PDF	2728185 d2af9013db8d2830af80430d49955194dbdc98ad	no	52
<b>Warnings:</b>					
<b>Information:</b>					
19	NPL Documents	Cerofolini_et_al_2000_196-202.pdf	510141 f02a75c96da7e7824f9b06bdac7e7c64f94c5a	no	7
<b>Warnings:</b>					
<b>Information:</b>					

20	NPL Documents	Chu_Ion_Implantation_In_Semiconductors.PDF	499300 9f888f682ac68f44945f7f10540d17e8f05595bec	no	12
<b>Warnings:</b>					
<b>Information:</b>					
21	NPL Documents	Chu_PK_Plasma_Immersion_Ion_Implantation.pdf	245084 88a37615da78c2753b0c0b984b0b795e24e0c797	no	5
<b>Warnings:</b>					
<b>Information:</b>					
22	NPL Documents	Chu_WK_et_al_Radiation_Damage_of_50-250_keV_Hydrogen.pdf	663443 54f08ec29f8b0b0c0f6b0bca790f9b0c1d47a1a5	no	10
<b>Warnings:</b>					
<b>Information:</b>					
23	NPL Documents	Cowen_N_et_al.pdf	499500 81c0da76d4f7229f0c1106d795f0f0a2a8f0e5b0c	no	8
<b>Warnings:</b>					
<b>Information:</b>					
24	NPL Documents	Cristoloveanu_S_et_al_Electrical_Properties_of_Unibond.pdf	157840 94d8116d4574e1901ec303421f5004e0cd3247	no	3
<b>Warnings:</b>					
<b>Information:</b>					
25	NPL Documents	Csepregi_I_et_al.pdf	125356 c7c7818d42491111d0c70f8ec21aee0dd1a2533	no	2
<b>Warnings:</b>					
<b>Information:</b>					
26	NPL Documents	Cullis_AG_et_al.pdf	660281 26c7d74d6d1226168532140298ced0dd0ff6a18	no	11
<b>Warnings:</b>					
<b>Information:</b>					
27	NPL Documents	Demeester_et_al.pdf	1057147 e514a07e257a78c09cdf8a60d19a80590ca40b7c	no	13
<b>Warnings:</b>					
<b>Information:</b>					
28	NPL Documents	Denteneer_et_al_1989_979-984.pdf	299205 9a9be761628b4f56107910a24c1956759a6b8a	no	5
<b>Warnings:</b>					
<b>Information:</b>					

29	NPL Documents	Denteneer_et_al_April_1989.pdf	342276 a9185aedf086a9e74e6c4a52627a5ce12a6a	no	4
<b>Warnings:</b>					
<b>Information:</b>					
30	NPL Documents	DiCioccio_et_al_1997_349-356.pdf	744238 d8c8b2811871ed78d4f4a5a1e5e4562059e486ad	no	8
<b>Warnings:</b>					
<b>Information:</b>					
31	NPL Documents	DiCioccio_et_al_1996_1144-1145.pdf	130526 f1f64628f8bb87ee5d472574c99b298302a4	no	2
<b>Warnings:</b>					
<b>Information:</b>					
32	NPL Documents	Diem_et_al.pdf	846924 149415-ab87ced3f9ed8f05d2ebacde812d999bc3	no	10
<b>Warnings:</b>					
<b>Information:</b>					
33	NPL Documents	Dirks_et_al.pdf	1187199 d9d89b5560b3cbe538baa781ca71cc23e786c3	no	15
<b>Warnings:</b>					
<b>Information:</b>					
34	NPL Documents	Duo_et_al_Comparison_Between_The_Different.pdf	821079 6219e4d26a98aed37c9d5489b517ddab7ca0d8	no	6
<b>Warnings:</b>					
<b>Information:</b>					
35	NPL Documents	Duo-et-al-Evolution-of-Hydrogen-and-Helium_1.PDF	549396 0c374771d8074bc6d548aa1070f66ae63f281a3	no	6
<b>Warnings:</b>					
<b>Information:</b>					
36	NPL Documents	Eaglesham_White_et_al_Equilibrium_Shape_of_Si.pdf	272298 5602dx891cd7781d2545788cf7de7e3d289fb	no	4
<b>Warnings:</b>					
<b>Information:</b>					
37	NPL Documents	EerNisse_E-Compaction_of_Ion-Implanted_Fused_Silica.pdf	768866 8ae542aa7094713b1395763d293a3138173c2	no	8
<b>Warnings:</b>					
<b>Information:</b>					

38	NPL Documents	EerNisse_EP- Role_of_Integrated_Lateral_Str ess_In_Surface.pdf	801341 c1e6258efad7556111b6a2253dc5f9bdc 1a79	no	9
<b>Warnings:</b>					
<b>Information:</b>					
39	NPL Documents	Evans_JH_An_Interbubble_Fra cture_Mechanism_Of_Blister. pdf	869679 da7e36619b716359bc79ee119144cfc5de 884b	no	12
<b>Warnings:</b>					
<b>Information:</b>					
40	NPL Documents	Feijoo_et_al- Prestressing_of_Bonded.pdf	390788 6e4546b0947157ac6b3bed111218dc3bce 16443	no	9
<b>Warnings:</b>					
<b>Information:</b>					
41	NPL Documents	Feng_et_al.pdf	137308 7bc09b79763717ce52afababefb051b29 05415	no	3
<b>Warnings:</b>					
<b>Information:</b>					
42	NPL Documents	Fukitsuka_et_al.pdf	488514 e3b62ae358900bf91e7417c53474d27ea79 9856	no	4
<b>Warnings:</b>					
<b>Information:</b>					
43	NPL Documents	Garnier.pdf	376649 3db2d6c6d96c7e912900f8a183803db263 5f5d24	no	6
<b>Warnings:</b>					
<b>Information:</b>					
44	NPL Documents	Gerasimenko.pdf	423407 fbad7bbabcf378bce6dc753dca0b1e1263c 2dc62	no	7
<b>Warnings:</b>					
<b>Information:</b>					
45	NPL Documents	Ghandi.pdf	145184 d4b5200b786a70c5146ebc11ba0f901416e 7917	no	4
<b>Warnings:</b>					
<b>Information:</b>					
46	NPL Documents	Goesele_et_al_Semiconductor _Wafer_Bonding.pdf	1371808 2c08f9dcb7bd07e6538f4d531171dc2c4e52 7fad	no	28
<b>Warnings:</b>					
<b>Information:</b>					

47	NPL Documents	Greenwald_et_al.pdf	364299 2f84ac2ee753b21736056630131285cf2416d8aa	no	4
Warnings:					
Information:					
48	NPL Documents	Grovenor_C_Microelectronic_Materials.pdf	183072 d46eb94d6295257bb1c504f92e143c3079d209f	no	5
Warnings:					
Information:					
49	NPL Documents	Guilhalmenc_C_et_al.pdf	266316 4eeb060d5b4c4d30065b74b1b38db1c35eb1	no	4
Warnings:					
Information:					
50	NPL Documents	Hamaguchi_et_al_688-691.pdf	308961 b2281928d488256918579a21f305a1058dbaf	no	4
Warnings:					
Information:					
51	NPL Documents	Hamaguchi_et_al_Device_Layer_Transfer_Technique.pdf	157984 e2d417472ed61c245c0b4156a07b605c5a1ba	no	3
Warnings:					
Information:					
52	NPL Documents	Henttinen_et_al-Mechanically_Induced_Si_Layer.pdf	248942 084a59b98ac7d3bbf9a6d17752ad4129ae93ac1	no	3
Warnings:					
Information:					
53	NPL Documents	Huang_et_al.pdf	77104 6c21652acc20061641c86d641284e09a24e57	no	3
Warnings:					
Information:					
54	NPL Documents	Hulett_DM_et_al_Ion_Nitriding_and_Ion_Impantation.pdf	228302 894673d4181b797acde886eb509d9cd13534052	no	4
Warnings:					
Information:					
55	NPL Documents	IBM_August.pdf	31620 6441c8f725df6ee6a3370ebf8aac6ac05176c	no	1
Warnings:					
Information:					

56	NPL Documents	IBM_July_1996.PDF	135377 a8d7768b42462068a7b78f173bc37d4d16e8b6a1	no	5
Warnings:					
Information:					
57	NPL Documents	Jalaguier_1998_408-409.pdf	459112 8bae91aef74a39bdebf66d88a653b31a18b38e436f3	no	2
Warnings:					
Information:					
58	NPL Documents	Jalaguier_et_al_1999_26-27.pdf	204439 0be7a05c11c1462b5846a2a3a1638b257cdd9d8	no	2
Warnings:					
Information:					
59	NPL Documents	Jaussaud_C_et_al.pdf	393224 8bc5a0b61d678876f6d6338055465a6be0e11	no	3
Warnings:					
Information:					
60	NPL Documents	Johnson.pdf	837642 4618896ca2172007db397a2d54022d639f6e437f	no	9
Warnings:					
Information:					
Total Files Size (in bytes):			31687014		

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

#### **New Applications Under 35 U.S.C. 111**

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

#### **National Stage of an International Application under 35 U.S.C. 371**

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

#### **New International Application Filed with the USPTO as a Receiving Office**

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.